Engineering Tripos Part IA 2002

Paper 3, Electrical and Information Engineering

Section A - Numerical Answers

1. (b)
$$R_o = 2304\Omega$$
; $X_o = 758 \Omega$; $R_t = 1.6 \Omega$; $X_t = 8.9 \Omega$

(c) (ii)
$$\theta_{TOTAL} = 530 \text{ VAR}$$
; $C = 29.3 \mu F$

2. (b) (ii)
$$V_{oc} = 25 \text{ V}$$

(iii)
$$V_{\text{meas}} = 22.2 \text{ V}$$

(iv)
$$R_{in} \ge 24.9 \text{ k}\Omega$$

(c) 11.2 % error

3. (c) (i)
$$Z_{in} = \frac{R_1 R_2}{R_1 + R_2}$$

(ii)
$$Z_{out} = \frac{R_s r_d}{R_s + r_d + g_m R_s r_d}$$

$$(iii) \qquad \frac{v_{out}}{v_{in}} = \frac{g_m}{g_m + \begin{bmatrix} R_s \pm r_d \\ R_s r_d \end{bmatrix}}$$

(d) [e.g.]
$$R_1 = R_2 = 2 \text{ M}\Omega$$
; $R_S = 1978 \Omega$

4. (c) gain =
$$\frac{-R_2}{R_1 + jwL}$$

(d)
$$L = 15.9 \text{ mH}$$

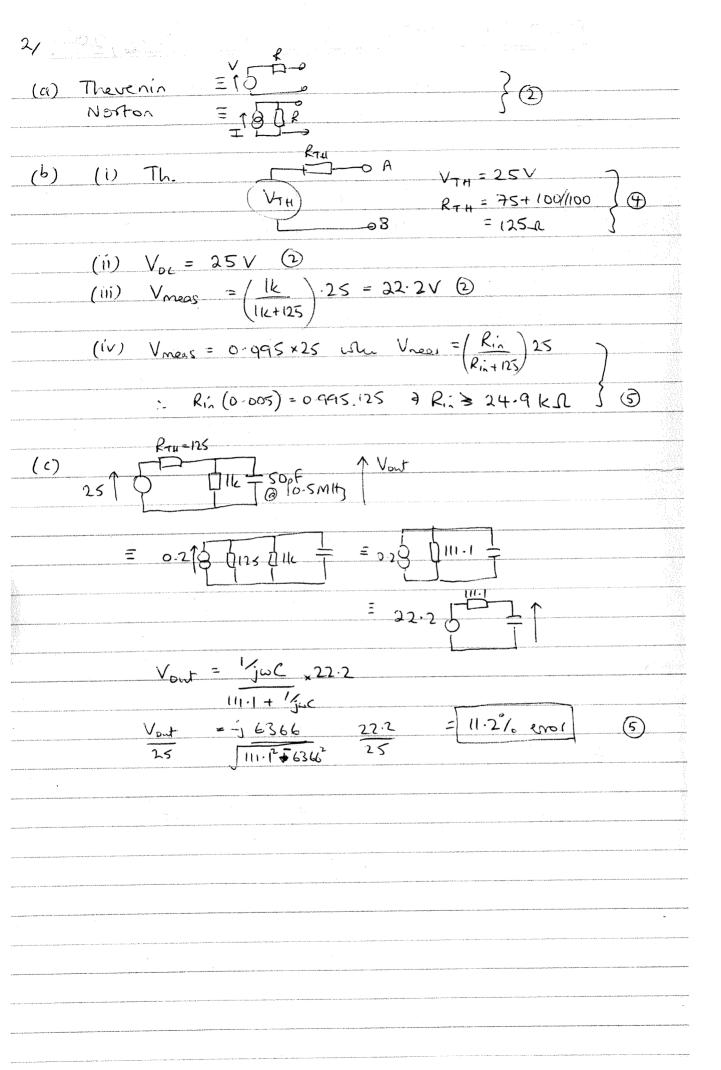
(e)
$$A = 1.99$$
; $B = -1.47$ [or equivalent]

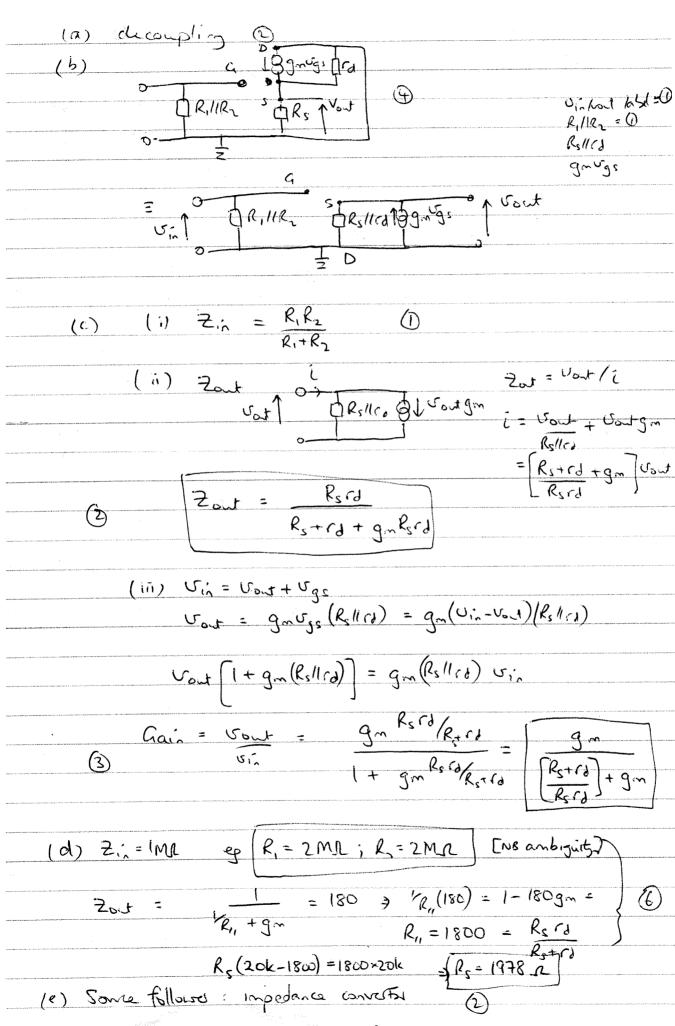
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RJM/vg 15/8/02

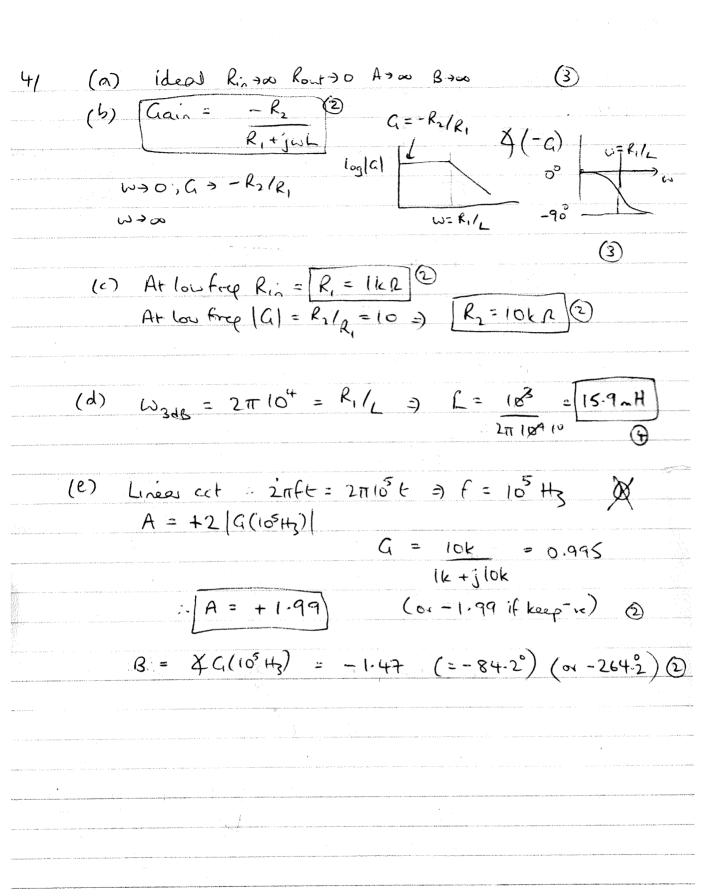
PART 1A, PAPER 3, SECTION A CRIB, 2002

(i) ideal? an loss 1/ (0) (ii) X,? Leakage induction (3) Total (7) (iii) Magnetising X., R. Ro = V2/P = 2402/25 = 23011_1 (b) (0 (2) X0 = V2/Q = 240 /(V17-P2 = 240 /72-25 = 853/L Total 6 Twos ratio = 2 = N, /N2 (NB At SOH (5) Xr = 0/Is = 1(NI)5 bs/Is = 8.89 U (0) (c) 3 200mH jul=j62-8 (3) : Total L= ;71.7 (ii) PLOAD = VI, COLD = 397 Wath Quan = 462 Var Q TOTAL = 529.5 VAR ANS = V2 WC = QTOT > C = 29-3 MF (2)





4-



Engineering IA 2002

Paper 3, Electrical and Information Engineering

Numerical answers

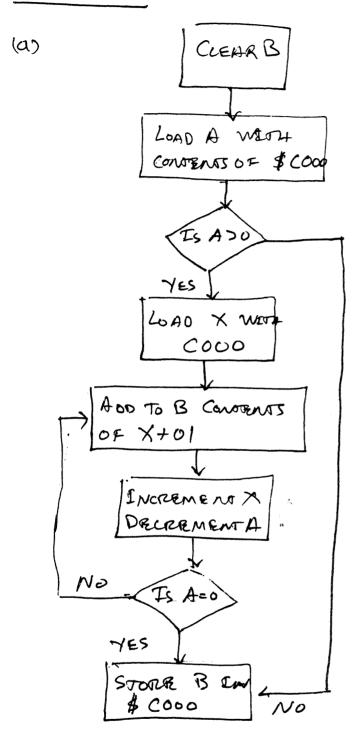
- 5) (c) 26 FA,
- (d) (i) The program will add three numbers. The result is 2A,
- (d)(ii) 32.5 μ s.
- 6) (b) NAND gate

(c) (iv)
$$F = \overline{B} + \overline{C}\overline{D} + CD$$
, $I = C\overline{D} + \overline{B}\overline{D}$

7) (b) OR gate

8) (c)
$$J_A = BM$$
, $K_A = B + \overline{M}$, $J_B = \overline{A} P$, $K_B = A + M + \overline{P}$

QUESTION 5:



- (b) ADD TO B THE CONTENTS OF MEMORY LOCATION

 AFTER THE MEMORY LOCATION STORRD IN INDEX

 RRGESTER X, USE) INDEXED ADDRESSENG
- (2 BYTES), INX (I BYTE), DECA (I BYTE), BNE (ZBYTES)
 TOTAL -6 BYTES, FAIN Z'S COMPLEMENT, 00 Z6 FA

- (d)(i) THE PROGRAMM WILL ADD 3 NUMBERS 05+0A+1B = ZAH
 - (ii) Cloch CYCLES

 2+4+2+4+3+5+4+2+4+5

 × 3

 TOTAL 65 CYCLES × 0.5 MS/ = 32.5 MS

MOST STUDENTS WERE ABUR TO FIGURE OUT WHAT
THR PROGRAM IS SUPPOSED TO DO & DRAW A
ROUGH FLOW CHART TO REPRESENT ITS OPERATION.
RELATIVELY FEW SUCLERDED IN GRATEN AU THE
DRIAILS OF THE FLOW CHART REGAT. THE MAJORITY
OF STUDENTS MADE MESTANES IN READENG FEGURES
FROM THE DATA BWOM (e.g. PART du) AND EN
THE (ALCULATIONS (du) AND RESPECEMBLY (C)).

QUESTION 6:

(a) RAM: RANDOM ACCRS) MEMORY, CAN BR READ FROM WRITTEN TO BY MECROPROCESSOR, NOLASTUR, CONTENTS COST IF POWER IS REMOVED.

ROM: READ ONLY MEMORY. CONTENTS CAN NOT BE CHAMBED BY MICROPROCESSOR. PERMANENT DATA REMAINS RURN WESTIONS POWER.

EPROM: ERASABLE, PROGRAMABUR ROM. SIMELAR FUNCTION TO ROM. CAN BE ERASED USENO BPRCIAC HIGH VOLTAGE PROGRAMMER DEVICE (OR SOMROTIMES UV LEGAT) AND REPROGRAMMED USENG HIGH VOLTAGRS

HARD DESUR: UNUSHE THR RRIT USR, MAGNETIC DISH FOR LONG TERM STORAGE. PERMANENT. HIGH CAPACETY, CON SPERD. PRAD/WRITE.

(b)
$$\gamma = AB + \overline{AB + BC}$$

= $\overline{AB + AB \cdot BC}$
= \overline{AB}

(DE MORGAN) (ABSORPTION)

(e)(i) TREVIAC

(i) 5 → 1011011] → 1110000 (1, ALSO O.K.)

(iii)

F:

ABCD	00	01	111	10
00	1	1	1	1
01	1	0	\	Ь
1/	7	X	X	×
10	1	1	7	×

	ABCD	00	a d	11	10
:	00	J	O	0	Ti-
	01	0	0	0)
	11	イ	X	×	×
	10	1	0	メ	×

 $I = C \cdot \overline{D} + \overline{B} \cdot \overline{D}$

OTHER COMBINATION WEST SAME NO OF TERMY POSSIBLE.

MOST STUDENTS PORUDUCED RESONABUR ANSWERS
TO (Q) AND (b). THE MANEPULATIONS OF THE
FORMULAS EN 16) WAS UNINTERSSATELY COMPUCATED
IN SOME CASES, OFFEN LEADENS TO MISTANES &
WASTENS TIME. PART (C)(i)-(iii) WERE ASSO
DONE WELL. MANY STUDENTS FACUED TO SPOT THE
SIMPLEST FORMULAS FOR (C)(iV).

QUESTION 7:

(a) NMOS: COMPACT, SLOW, CHRAP, RRLATTIRLY
HEGA POURR CONSUMPTION.

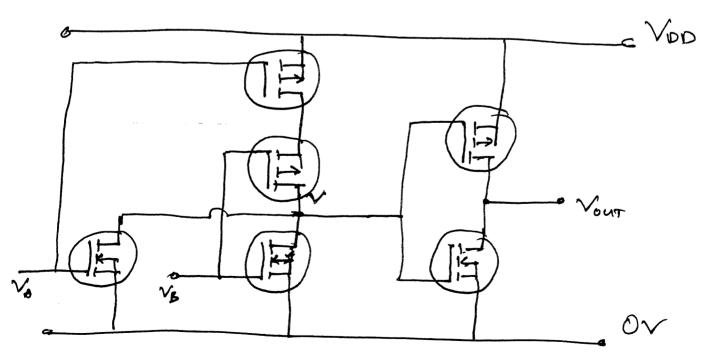
CMO): MAX CLOCH FREQUENCY 12-40 MHZ. LOW POWER CONSUMPTION (POWER CONSUMED ONLY DUREM STORE TRANSFORMS)

TTL: FAST (35-200 M HZ), HEGH POWER, BASRO IN BERNAR TRANSESTORS

ECL: VERY HEGA SPERD, HIGH POWER. DUSO BIRDAR.

(b) THE CERCULT IS AN OR GAME. WHEN VA AND/OR VB ARE HIGH, TI AND/OR TZ ARE ON, THEREFORE VIS LOW, THEREFORE TS IS OFF, AND VOUNT IS HIGH. WHEN VA AND VB ARE BOTH LOW, TI AND TZ ARR OFF, HENCR VIS HEGH, TS IS ON AND VOUNT IS LOW.

CMOS CERCUIT



(C) THE ONE OUT OF 2" ADDRESS DECODER HAS Y INDUT
WIRES (CONNECTED TO THE ADDRESS BUS) AND 2" OUTPUT
WERED (CONNECTED TO MEMORY RUEMENTS).

AN ADDRESS IS ENCODED AS ABENDEY NUMBER ENTHE
M INPUT BETS. THE DREODER MAKED THE (ONE-OUT-OF-2")

OUTPUT WERE (OPERSPONDENT TO THE ADDRESS HEGA,

A 1- OWA-OF- 32 DECODER MAY LOOK LEHE THES

A1 OO OI

AND THR RAMAINERS 27-1 OUPUT WERES LOW.

(d) A Is THE OUTPUT OF AN ADDRESS DRUDER. IT IS HECH WARNEVER WE ARR READENS/WELTING TO THE MEMORY LOCATION CONTAINENT THE ELEMENT, AND LOW OTHERMESE.

LES THR DAGA FROM THR ENRICHER LOSEC. IT MAX GET STORRD EN THR EURMENT ER A AND WARR HESH

LOW BTHERNESE

HEGHER ADDRESSES.

THE AVERAGE MARN WAS FAIRLY LOW FOR THIS QUESTION. MOST STUDENTS DID OK IN PARTS (Q) AND (C). RELATIVELY FEW REMEMBERED THE ANSWER TO Cd). VERY FEW WERE ABUR TO DEFERMINE THAT THE CERCULT IN (6) IS AN "OR" GATE. VERTUALLY NOWE WAS ABUR TO INTRODUCE THAT PMOS TRANSISTORY CORRECTLY.

QUESTION 8:

SOOR	A	B
\mathcal{I}	0	0
W	0	1
5	(O
\cup	(

(6)	$ \begin{array}{c c} P=0 \\ M=x \\ \hline M=x \\ \hline \end{array} $
	P=x P=1 P=0 M=0
P=X M=1	10 P=x 01 = 1 = 0

(c)	In	JPUT	STATE	NEXT	ì	
	P	^	A B	AB	JA KA	JB KB
	O	x	0 0	0 0	0 ×	0 ×
		\prec	00	1	o ×	1 ×
	0	0	0 1	00	0 ×	× 1
	1.	0	0 1	0 1	0 ×	× o
	X	1	0 1	10	ΐ×	XI
	X	0	10	00	× 1	OX
	X	1	1 0	(0	XO	OX
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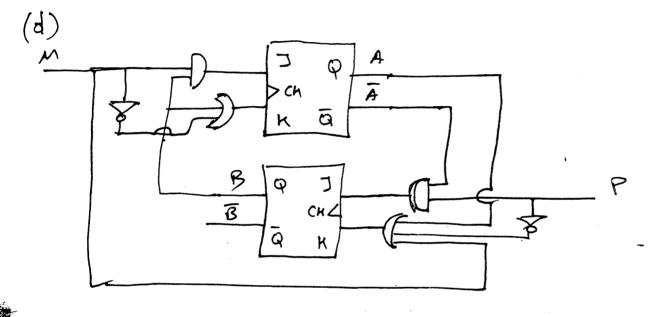
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00	O	8	X	X	<u></u>
6/	0	١	X	×	l JA
1)	0	١	×	X	_
10	0	0	7	×	•

	PMARS	00	01	11	10	
	00	X	X	1)	_
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	10	X	×)	1	Water and Personal Property and Publishers of the Personal Property and Personal Propert

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11 1 7 7 0	01	O	×	7	0	JB
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J	R	_	A	•	P
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	PMB	00	01	111	110	1
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	17	×	,	١	×	-
	10	×	0) /	×	
	•	1	,			



PARTS (a) AND (b) WERE MORR OR LRSS TREVER(.
MANN PROPUR WASTED RASY INARMS BY NEGLEUTING
TO DRAW STOOTR DEAGRAMS, ALLOCATION TABLES, ETC.
MOST STUDENTS DED OK IN PART (C). SOME DID NOT
MANR USE OF "WELD CARDS" LRADING TO SMALL
MESTANRS AND/OR UNNRERSSARILY COMPLECATED
OCCCULTS IN PART (d)

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Numerical answers

9. a)
$$C = \frac{A\varepsilon_0\varepsilon_r}{x}$$

b)
$$F = \frac{1}{2}V^2 \frac{dC}{dx}$$

- c) 0.22mN (no edge or fringing effects)
- d) 334 kV
- 10
- b) 1.33 Tesla
- c) 3.54 A
- d) 140 N
- 11

c)
$$\frac{\sqrt{2}\mu_0 I}{\pi} \frac{n}{b-a} \ln\left(\frac{b}{a}\right)$$
 --- assuming n is large

Exam crib

9. a)

Gauss's Law:

 $\iint_{S} \underline{D.dS} = Q \quad \text{--- The total electric flux emerging from any surface is equal to the charge enclosed by that surface. Colloquially electric flux lines begin and end on charges.}$

From Gauss's law we get (assuming that there are no fringing fields and consequently that the electric field lines pass perpendicularly between the plates and that D can therefore be treated as a scalar quantity)

D*A = Q where A is the area of the plates

But

$$D = \varepsilon_0 \varepsilon_r E \qquad \Rightarrow E = \frac{q}{A \varepsilon_0 \varepsilon_r}$$

$$V = \int E dx$$

= $\frac{qx}{A\varepsilon_0\varepsilon_r}$ Where x is the separation of the plates

Since
$$q = CV$$
 $\Rightarrow C = \frac{A\varepsilon_0 \varepsilon_r}{x}$

b) NB: the following analysis assumes constant charge q

from work

$$-F\delta x = \frac{1}{2}q\delta V$$

Hence in the limit:

$$F = -\frac{1}{2}q \frac{dV}{dx}$$
Also: $V = \frac{q}{C}$ $\Rightarrow \frac{dV}{dx} = -\frac{q}{C^2} \frac{dC}{dx}$

And therefore
$$F = \frac{1}{2}V^2 \frac{dC}{dx}$$

c) Using the expression for capacitance derived in part a) we obtain:

$$\frac{dC}{dx} = -\frac{A\varepsilon_0 \varepsilon_r}{x^2}$$
Force = $(\frac{1/2*100*0.1*5*8.854*10^{-12}}{10^{-6}})$
= 0.22mN

As stated above there are no edge or fringing effects

d) Starting from Young's Modulus

$$E = Stress / Strain = Force / Area / (1/200)$$

We get

$$F = \frac{EA}{200}$$

We also know that:

$$F = -\frac{1}{2}V^{2} \frac{A\varepsilon_{0}\varepsilon_{r}}{x^{2}}$$

$$V^{2} = \frac{2E}{200\varepsilon_{0}\varepsilon_{r}}x^{2} = (100*10^{9}*0.995*10^{-6}*2/200*1000*8.854*10^{-12})^{1/2}$$

= 334 kV --- This figure is actually rather high and in practice would probably not be achieved due to breakdown of the dielectric

Note:

This question is a fairly straightforward application of Gauss's law which was very well answered by most students despite the inclusion of Young's modulus in the final part! Some students chose to derive the expression for force by assuming constant voltage rather than constant charge.

10

a)
$$\iint_{c} \underline{H} \cdot \underline{dl} = \int_{s} (\underline{J} + \underline{D}) \underline{ds}$$
: For the purposes of first year work we ignore the term in \underline{D}

(Maxwell's displacement current) and then the interpretation of Ampere's law is that if you draw any closed loop and integrate H around that loop the answer you arrive at will equal the total current (current density J * area) passing through that loop. It is especially useful in tasks such as tranformer design where the right hand side is usually the total current expressed in terms of ampere turns i.e. the current through the coil times the number of loops in the coil.

b) For the magnetic circuit we can write down the following, since there is initially no current in the coil.

$$H_{iron}d_{iron} + H_{magnet}d_{magnet} = 0$$

We treat the iron as a linear material and so can say:

$$B_{iron} = \mu_0 \mu_r H_{iron}$$

In addition we can apply conservation of flux and observing that the cross-sectional area is constant around the circuit we end up with:

$$B_{iron} = B_{magnet}$$

Substituting in:

$$\underline{\mathbf{B}_{\text{magnet}}} \ \mathbf{d}_{\text{iron}} + \mathbf{H}_{\text{magnet}} \mathbf{d}_{\text{magnet}} = 0$$
$$\mu_0 \ \mu_r$$

Hence

$$\begin{split} B_{magnet} &= -H_{magnet} \mu_0 \mu_r \left(\frac{d_{magnet}}{d_{iron}} \right) \\ &= -4\pi * 10^{-7} * 1000 * \frac{30}{370} H_{magnet} \\ &= -10.18 * 10^{-5} H_{magnet} \end{split}$$

From the graph for Columax in the Data Book we obtain

$$B_{magnet} = 1.33 \text{ Tesla}$$

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c) For this part we add in the effect of an electric current in the coil so Ampere's law reduces to:

$$H_{iron}d_{iron} + H_{magnet}d_{magnet} = nI$$

In this case B in the iron and the magnet is zero as the question states. We are treating Iron as a linear material so H in the iron is also zero so the above reduces to:

$$H_{magnet}d_{magnet} = nI$$

From the graph H for columnx when B is equal to nought is -5.9×10^4 A/m

Hence

$$I = 5.9 \times 10^4 \times 30 \times 10^{-3} / 500$$

$$I = 3.54 A$$

d) The force developed at the jaws of the clamp is given by:

$$F = \frac{B^2 A}{2\mu_0} = \frac{1.33^2 *100 *10^{-6}}{2 *4\pi 10^{-7}}$$
$$-70 N$$

However the load is applied at the midpoint of the hinge and the clamps jaws so the force developed is actually twice this

Force =
$$140 \text{ N}$$

NOTES: This question was generally answered well although part d calculating the force developed was often missed out. This could be because the students assumed it was harder than it actually was. A common mistake with part c was to use the value for H in the magnet which was calculated in part b.

11

a) Biot-Savart Law (in scalar notation)

$$dH = \frac{Idl \sin \theta}{4\pi r^2}$$
 The Biot-Savart law enables you to calculate the magnetic field at any

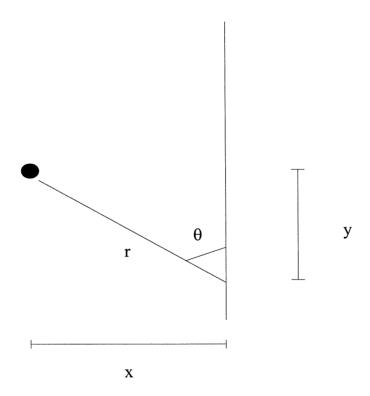
point by giving the contribution of each current element I dl. Integrating the expression over all current elements gives the total field at a particular point in space. In the equation r refers to the distance between the element and the selected point and theta is the angle between the current element and the line joining it to the selected point.

In free space we can rewrite the expression using B instead of H

$$dB = \frac{\mu_0 I dl \sin \theta}{4\pi r^2}$$

Note the expression is given in scalar notation as this is sufficient for first year work but B and for that matter H are both vectors and it is worth noting that the direction of B (or H) is perpendicular to the plane containing the current element dl and the selected point.

b)



$$B = \int_{-L/2}^{L/2} \frac{\mu_0 I}{4\pi r^2} \frac{r \sin \theta}{r} dl \quad \text{and} \quad y = l; x = r \sin \theta; r^2 = (x^2 + y^2)$$

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$$\Rightarrow B = \int_{-L/2}^{L/2} \frac{\mu_0 I x}{4\pi (x^2 + y^2)^{3/2}} dy = \frac{\mu_0 L I}{2\pi x (4x^2 + L^2)^{1/2}}$$

b) B at the centre of a square coil with a single loop is therefore given by:

$$B = \frac{2\mu_0 LI}{\pi x (4x^2 + L^2)^{1/2}}$$

Where x is the 'radius' of the coil, and, importantly, the side length of the coil is 2x

So the total B is given by

$$B = \sum_{n=0}^{\infty} \frac{2\mu_0 L_N I}{\pi x_N (4x_N^2 + L_N^2)^{1/2}} \quad and \quad L_N = 2x_N$$

$$= > B = \sum_{n=0}^{\infty} \frac{\sqrt{2}\mu_0 I}{\pi x_N}$$

Where

$$x_N = \frac{a}{2} + (N-1) \frac{\left(\frac{b}{2} - \frac{a}{2}\right)}{n};$$

Assume n is large and then integrate with respect to N we get:

We get

$$\frac{\sqrt{2}\mu_0 I}{\pi} \int_{1}^{n} \frac{1}{a + \frac{N-1}{n}(b-a)} dN = \frac{\sqrt{2}\mu_0 I}{\pi} \frac{n}{b-a} \ln\left(\frac{b}{a}\right)$$

Notes:

This question was attempted by very few students very few of whom managed to solve it. It is more a test of maths than engineering as the Biot-Savart law is quoted in the data book.